

IN THE CLAIMS

Kindly amend claim 1 and add new claim 12 as follows:

1. (currently amended) A tunable radio frequency (RF) band-pass filter provided with field effect (FET) capacitors arranged for controlling their respective capacity values, each such FET capacitor having a source (S) and a drain (D), characterised in that the source (S) and the drain (D) of each FET capacitor are coupled to one another at a common connection point, and said common connection points are coupled to each other through a capacitor, the tunable RF band-pass filter including an arrangement for tuning the tunable RF band-pass filter by selectively controlling the voltage dependent capacitor values of the FET capacitors, the tunable RF band-pass filter transforming an RF input impedance at a filter input to an RF output impedance at a filter output.

2. (previously presented) The filter according to claim 1, characterised in that each FET capacitor has a control input for voltage dependent capacity value control.

3. (previously presented) The filter according to claim 2, characterised in that the tuning arrangement is provided with control means coupled to the FET capacitor control inputs.

4. (previously presented) The filter according to claim 1, characterised in that the FET capacitors are split in equally controlled pairs of FET capacitors.

5. (previously presented) The filter according to claim 1, characterised in that the filter is built up as a symmetrical filter having a symmetrical input and a symmetrical output.

6. (previously presented) The filter according to claim 1, characterised in that two or more of the FET capacitors are connected in series.

7. (previously presented) The filter according to claim 1, characterised in that the FET capacitors are metal oxide semiconductor (MOSFET) capacitors.

8. (previously presented) A transmitter, receiver, or transceiver having a tunable radio frequency (RF) band-pass filter according to claim 1, which tunable RF band-pass filter is provided with field effect (FET) capacitors arranged for controlling their respective capacity values, each such FET capacitor having a source (S) and a drain (D), characterised in that the source (S) and the drain (D) of each FET capacitor are coupled to one another, the tunable RF

band-pass filter including an arrangement for tuning the tunable RF band-pass filter by selectively controlling the voltage dependent capacitor values of the FET capacitors.

9. (previously presented) The filter according to claim 1, wherein an input to the filter is coupled to a series arrangement of pairs of the FET capacitors.

10. (previously presented) The filter according to claim 9, wherein the series arrangement of pairs of the FET capacitors are split in equally controlled pairs of the FET capacitors.

11. (previously presented) The filter according to claim 1, wherein the tuning arrangement includes a decoder coupled to a gate of each of the FET capacitors.

12. (new) A tunable radio frequency (RF) band-pass filter according to claim 1, wherein each FET capacitor further comprises a gate (G), and each FET capacitor is controlled by a signal on said gate.